

Title (en)  
METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE WITH SCHOTTKY ELECTRODES

Publication  
**EP 0304073 A3 19910130 (EN)**

Application  
**EP 88113499 A 19880819**

Priority  
JP 20754087 A 19870821

Abstract (en)  
[origin: EP0304073A2] A method for manufacturing a semiconductor device with a Schottky electrode comprises the steps of subjecting the surface of a GaAs substrate (10) to a sputtering etching process in a sputtering processing chamber (1) of a sputtering device; and depositing Schottky electrode material by sputtering on the surface of the substrate (1) to form a Schottky electrode in the processing chamber (1) without exposing the substrate (10) to the atmosphere.

IPC 1-7  
**H01L 21/263**; **H01L 21/283**

IPC 8 full level  
**H01L 29/812** (2006.01); **H01L 21/263** (2006.01); **H01L 21/28** (2006.01); **H01L 21/285** (2006.01); **H01L 21/338** (2006.01); **H01L 29/47** (2006.01); **H01L 29/872** (2006.01)

CPC (source: EP KR)  
**H01L 21/2633** (2013.01 - EP); **H01L 21/28** (2013.01 - KR); **H01L 21/28581** (2013.01 - EP); **H01L 29/66863** (2013.01 - EP)

Citation (search report)

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Designated contracting state (EPC)  
DE FR GB NL

DOCDB simple family (publication)  
**EP 0304073 A2 19890222**; **EP 0304073 A3 19910130**; JP S6450527 A 19890227; KR 890004400 A 19890421; KR 910009315 B1 19911109

DOCDB simple family (application)  
**EP 88113499 A 19880819**; JP 20754087 A 19870821; KR 880010455 A 19880817